

PMV50UPE

20 V, single P-channel Trench MOSFET

20 July 2012

Product data sheet

1. Product profile

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- 3 kV ESD protected
- Trench MOSFET technology
- · Low threshold voltage

1.3 Applications

- · Relay driver
- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V	
V_{GS}	gate-source voltage			-8	-	8	V	
I _D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C; $t \le 5$ s	[1]	-	-	-3.7	Α	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -3.2 A; T_j = 25 °C		-	50	66	mΩ	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u></u> 3	D I
2	S	source		
3	D	drain	1	G S S 017aaa259

3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMV50UPE	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

4. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV50UPE	%CZ

^{[1] % =} placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}; t \le 5 \text{ s}$	[1]	-	-3.7	Α
		V_{GS} = -4.5 V; T_{amb} = 25 °C	[1]	-	-3.2	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-2	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-12.8	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	500	mW

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Symbol	Parameter	Conditions		Min	Max	Unit
			[1]	-	955	mW
		T _{sp} = 25 °C		-	3570	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode		,			
I _S	source current	T _{amb} = 25 °C	[1]	-	-1	Α
ESD maxim	num rating		,			
V _{ESD}	electrostatic discharge voltage	HBM	[3]	-	3000	V
	- I	1				

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

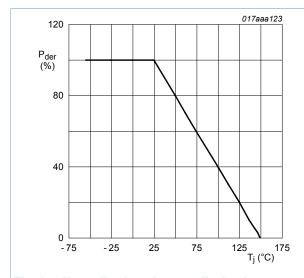


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

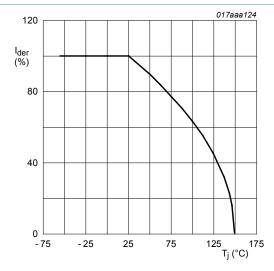


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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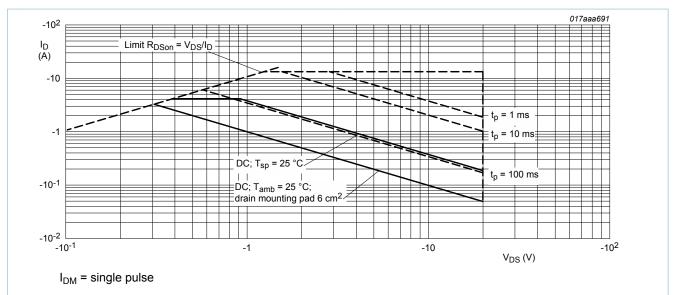


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1]	-	218	250	K/W
		<u>[2]</u>	-	114	130	K/W	
	ambient		[3]	-	80	92	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	30	35	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm², $t \le 5$ s.

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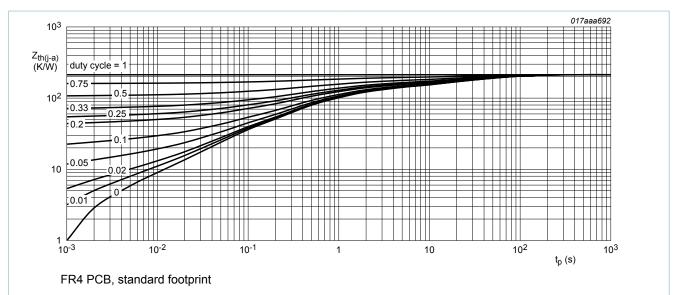


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

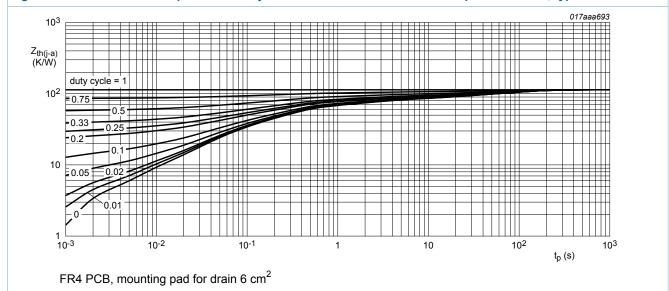


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static characteristics							,
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$		-20	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C		-0.47	-0.6	-0.9	V
I _{DSS}	drain leakage current	V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C		-	-	-1	μA
		V _{DS} = -20 V; V _{GS} = 0 V; T _j = 150 °C		-	-	-10	μA
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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{GSS}	gate leakage current	$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$		-	-	10	μA
		V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C		-	-	10	μΑ
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I_D = -3.2 A; T_j = 25 °C		-	50	66	mΩ
	resistance	V_{GS} = -4.5 V; I_D = -3.2 A; T_j = 150 °C		-	73	96	mΩ
		V_{GS} = -2.5 V; I_D = -2.1 A; T_j = 25 °C		-	57	81	mΩ
		V_{GS} = -1.8 V; I_D = -2.1 A; T_j = 25 °C		-	70	110	mΩ
g _{fs}	forward transconductance	V_{DS} = -5 V; I_{D} = -3.2 A; T_{j} = 25 °C		-	18	-	S
Dynamic cl	naracteristics						_
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -3.2 A; V_{GS} = -4.5 V; T_{j} = 25 °C		-	10.5	15.7	nC
Q _{GS}	gate-source charge			-	2.2	-	nC
Q_{GD}	gate-drain charge	1		-	2.7	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;		-	24	-	pF
C _{oss}	output capacitance	T _j = 25 °C		-	106	-	pF
C _{rss}	reverse transfer capacitance			-	14.6	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -3.2 A; V_{GS} = -4.5 V;		-	400	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$		-	700	-	ns
t _{d(off)}	turn-off delay time			-	2180	-	ns
t _f	fall time			-	8800	-	ns
Source-dra	in diode	1	1			1	
V _{SD}	source-drain voltage	$I_S = -1 \text{ A; } V_{GS} = 0 \text{ V; } T_j = 25 \text{ °C}$		-	-0.8	-1.2	V

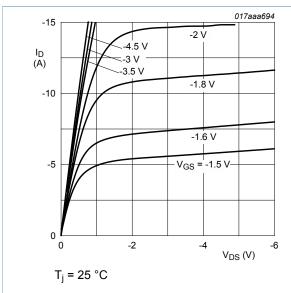


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

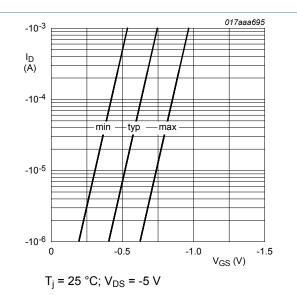


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

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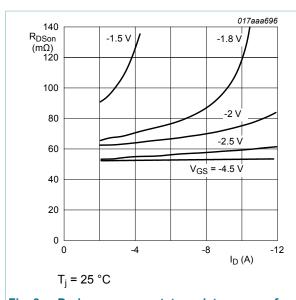


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

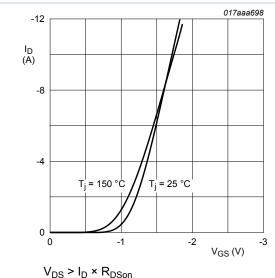


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

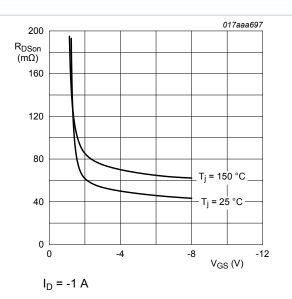


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

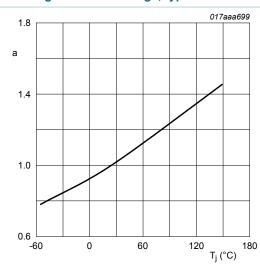


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

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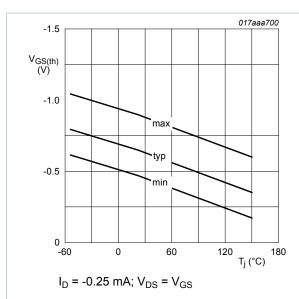


Fig. 12. Gate-source threshold voltage as a function of junction temperature

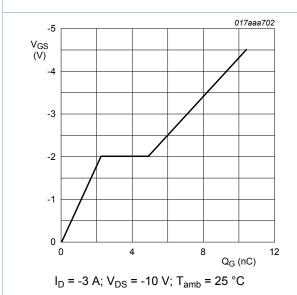


Fig. 14. Gate-source voltage as a function of gate charge; typical values

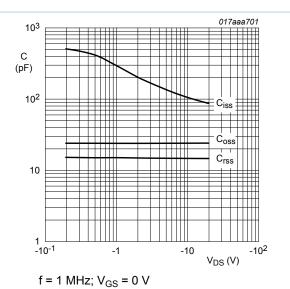


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical

values

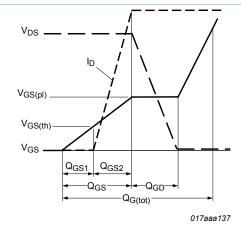
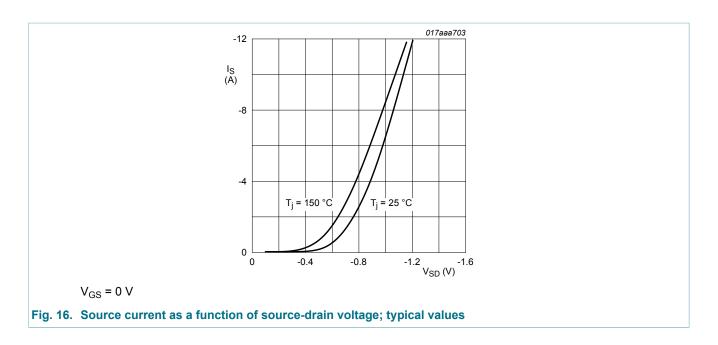
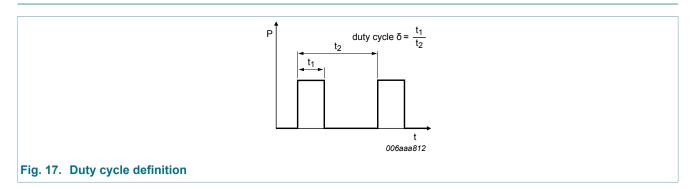


Fig. 15. Gate charge waveform definitions

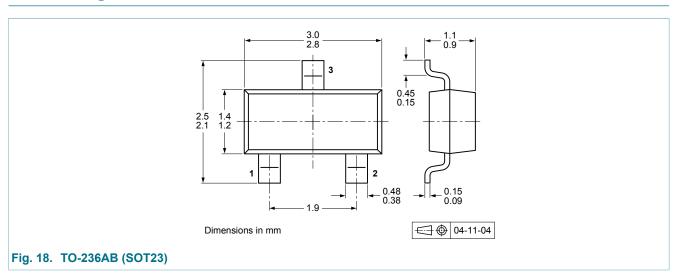
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8. Test information



9. Package outline

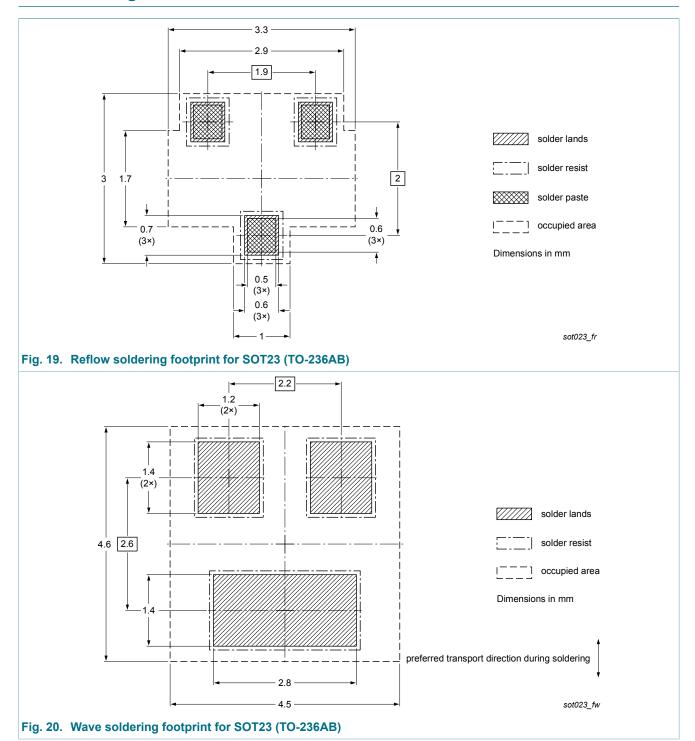


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10. Soldering



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11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV50UPE v.1	20120720	Product data sheet	-	-

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12. Legal information

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Product [short] data sheet	Production	This document contains the product specification.

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